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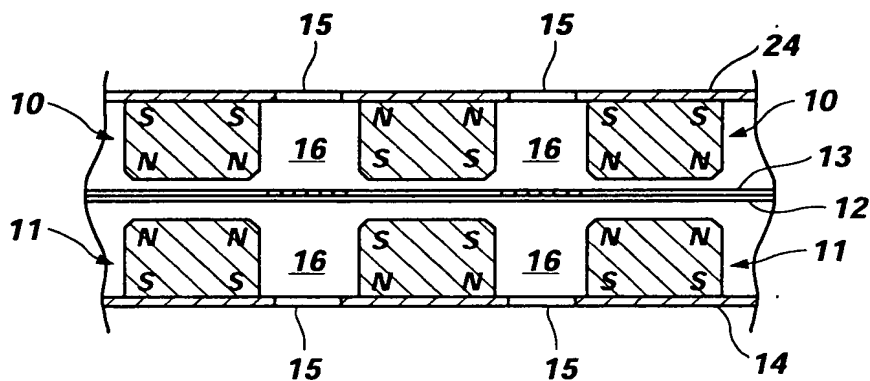


Fig. 1
(PRIOR ART)

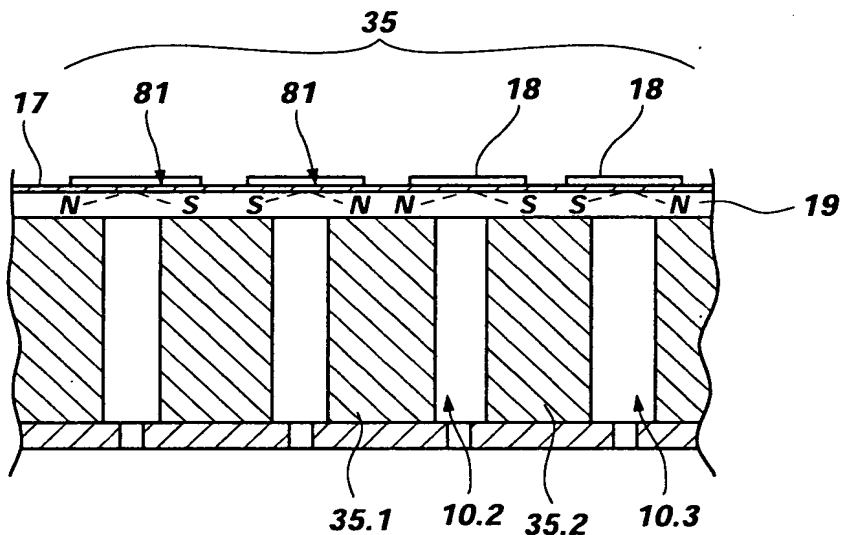


Fig. 2
(PRIOR ART)

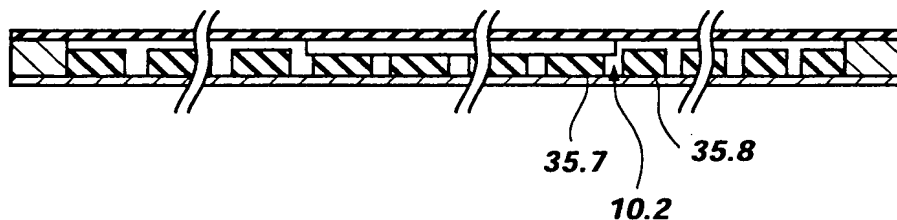
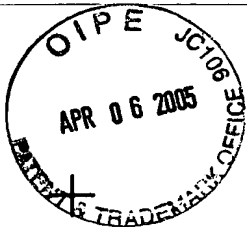


Fig. 3
(PRIOR ART)



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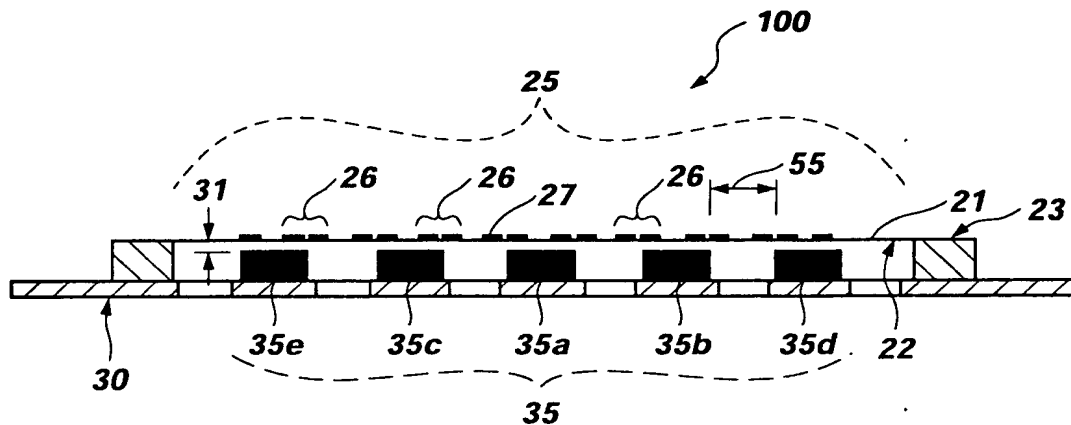


Fig. 4

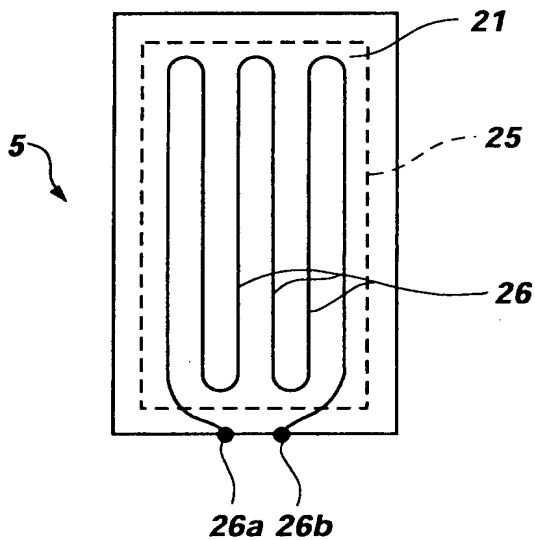


Fig. 5

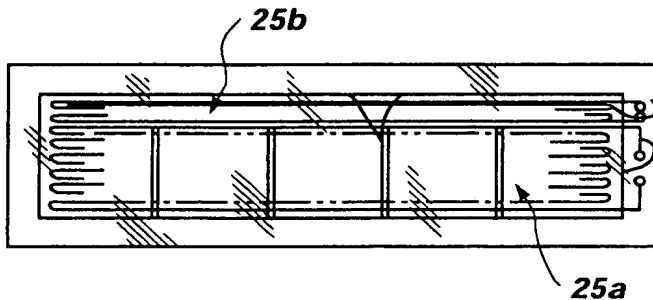


Fig. 6
(PRIOR ART)

A cross-sectional view of a semiconductor device 20. The device consists of a substrate 35a with a series of alternating black and white rectangular layers 35b and 35c. A thin layer 21 is deposited on top of these layers. Small rectangular features 26 are located on the top surface of the black layers 35b. A layer 35d is on the right side, and a layer 35e is on the left side. A dimension line 55 indicates the width of one of the black layers 35b. A group of lines 27 points to the top surface of the device.



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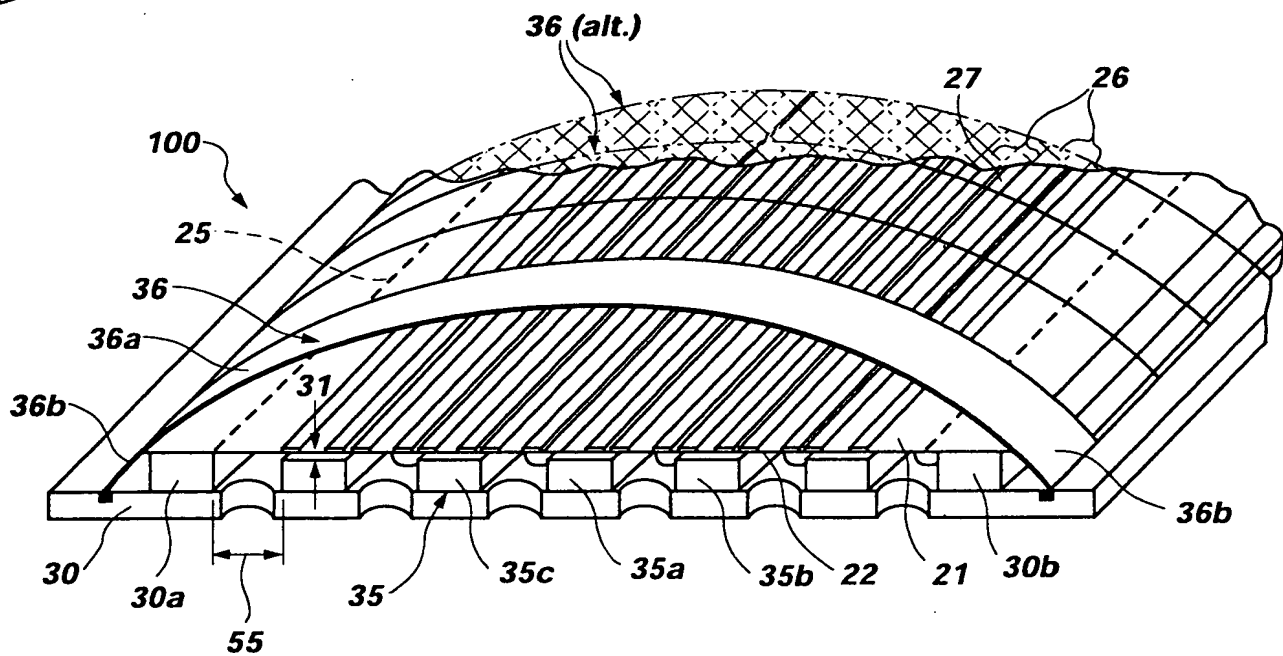


Fig. 15

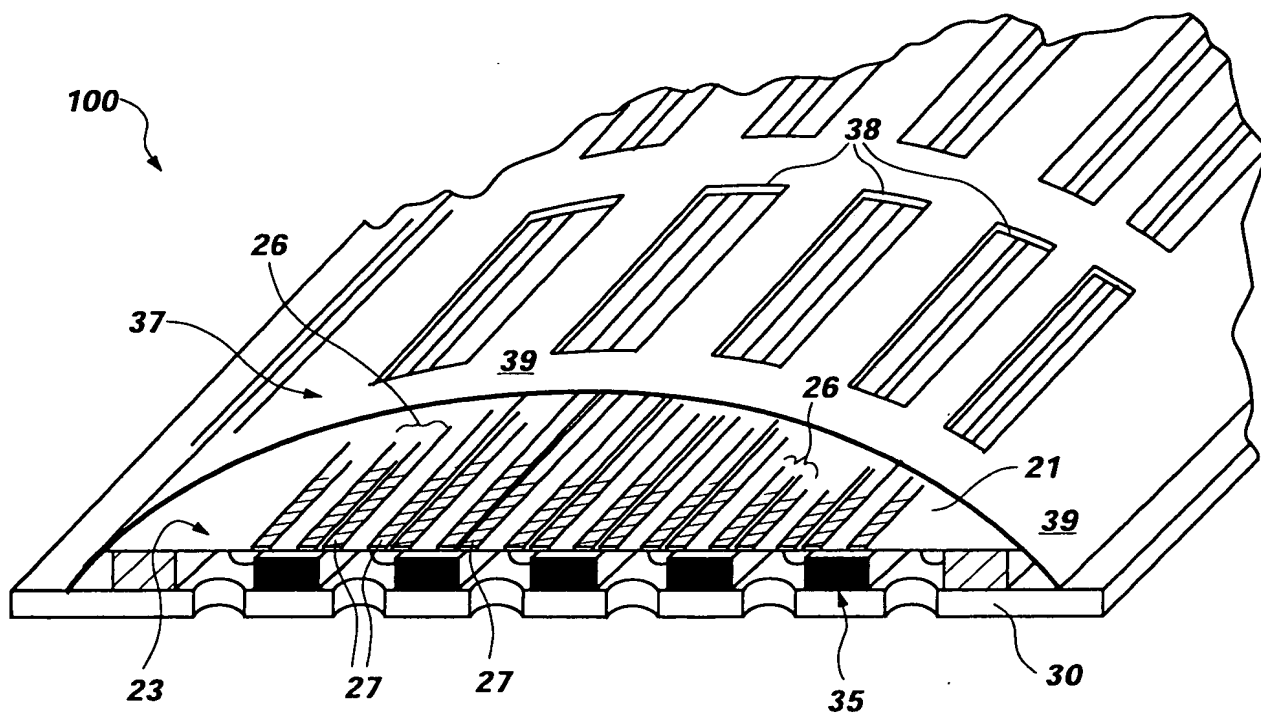


Fig. 16



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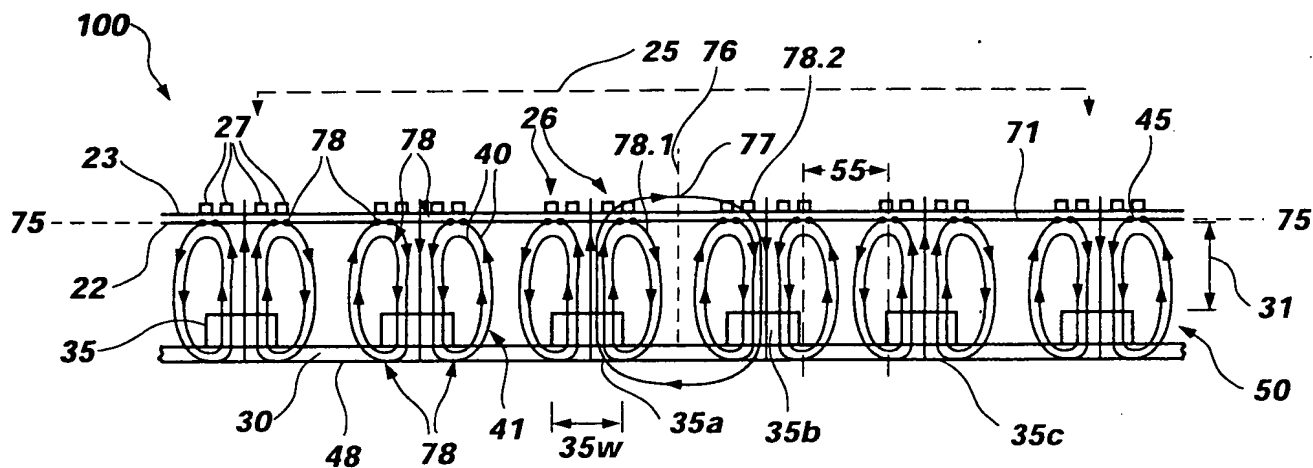


Fig. 26

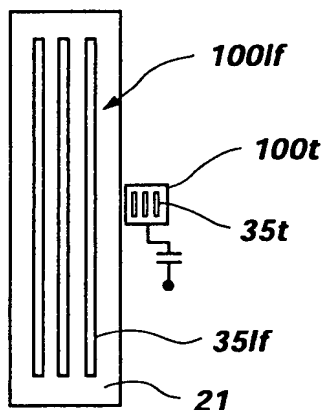


Fig. 24

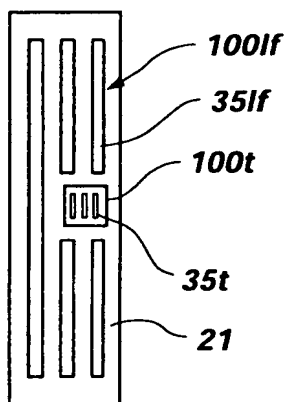


Fig. 25

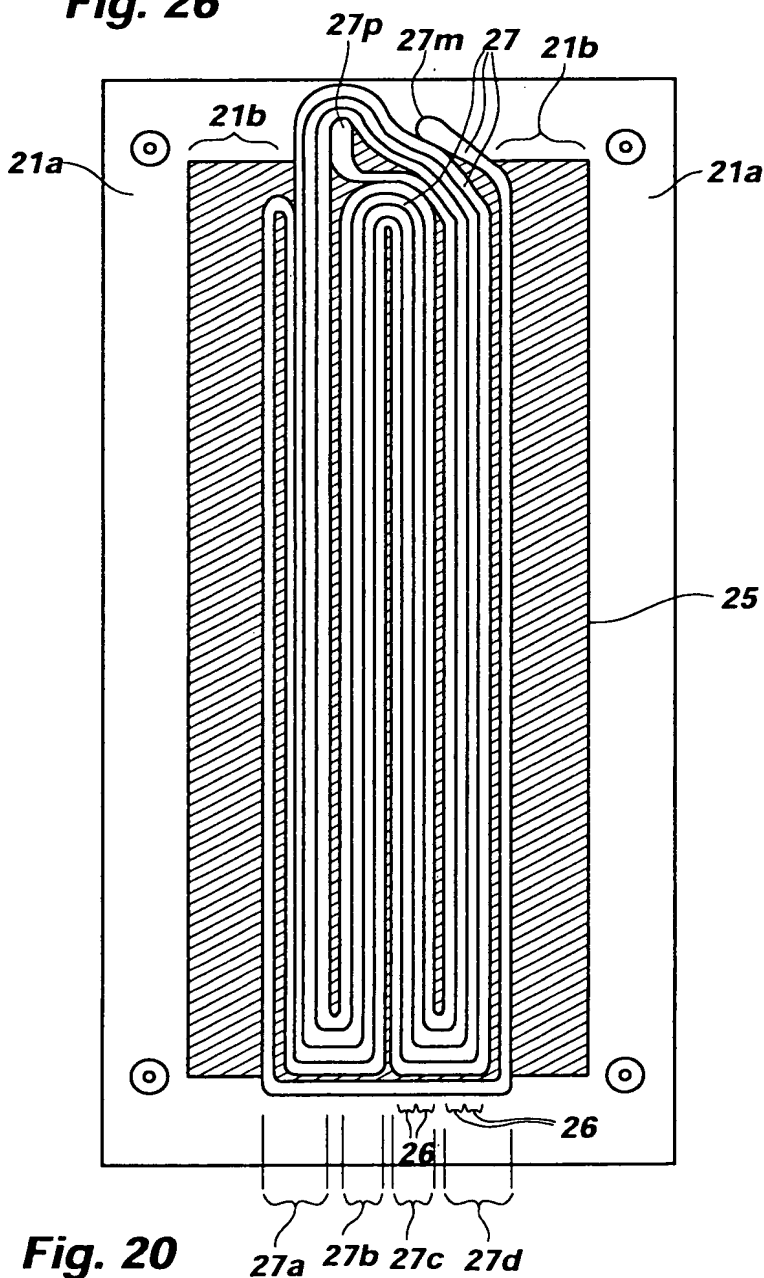


Fig. 20